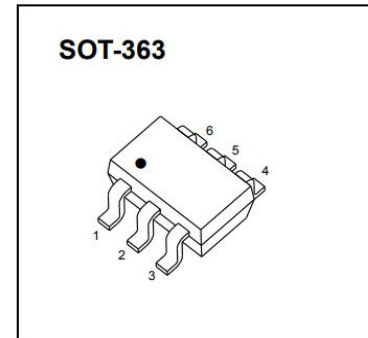


Plastic-Encapsulate MOSFETs

P-CHANNEL MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-50 V	8Ω@-10V	-0.13A
	10Ω@ -5V	



DESCRIPTION

These miniature surface mount MOSFETs reduce power loss conserve energy, making this device ideal for use in small power management circuitry.

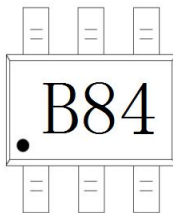
FEATURE

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- Miniature Surface Mount Package Saves Board Space

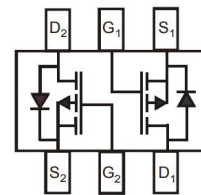
APPLICATION

- DC-DC converters, load switching, power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

MARKING



Equivalent Circuit



MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-0.13	A
Pulsed Drain Current (note 1) @tp < 10 μs	I_{DM}	-0.52	A
Power Dissipation	P_D	225	mW
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	556	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C
Maximum Lead Temperature for Soldering Purposes, Duration for 5 Seconds	T_L	260	°C

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-50			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -50V, V _{GS} = 0V			-15	μA
		V _{DS} = -25V, V _{GS} = 0V			-0.1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±5	μA
Gate threshold voltage (note 3)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.9	-1.6	-2	V
Drain-source on-resistance (note 3)	R _{DS(on)}	V _{GS} = -5V, I _D = -0.1A		5.8	10	Ω
		V _{GS} = -10V, I _D = -0.1A		4.5	8	Ω
Forward transconductance (note 1)	g _{FS}	V _{DS} = -25V; I _D = -100mA	50			mS
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C _{iss}	V _{DS} = 5V, V _{GS} = 0V, f = 1MHz		30		pF
Output capacitance	C _{oss}			10		pF
Reverse transfer capacitance	C _{rss}			5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	t _{d(on)}	V _{DD} = -15V, R _L = 50Ω, I _D = -2.5A		2.5		ns
Turn-on rise time	t _r			1		ns
Turn-off delay time	t _{d(off)}			16		ns
Turn-off fall time	t _f			8		ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
Continuous Current	I _S	I _S = -0.13A, V _{GS} = 0V			-0.13	A
Pulsed Current	I _{SM}				-0.52	A
Diode forward voltage (note 3)	V _{SD}				-2.2	V

Notes :

1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , t_s ≤ 10s.
3. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to producing.



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INTERNATIONAL

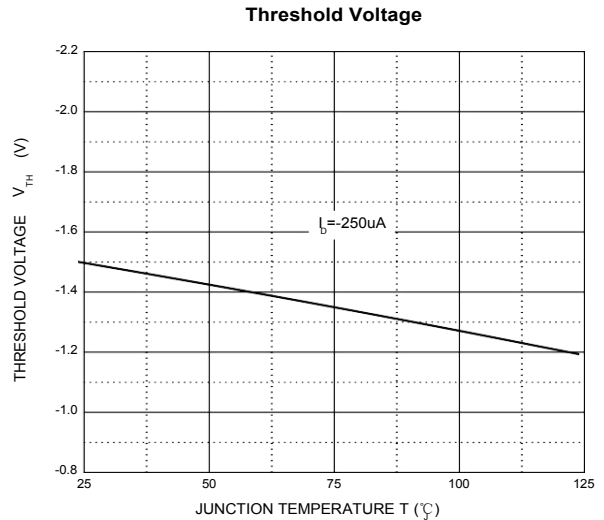
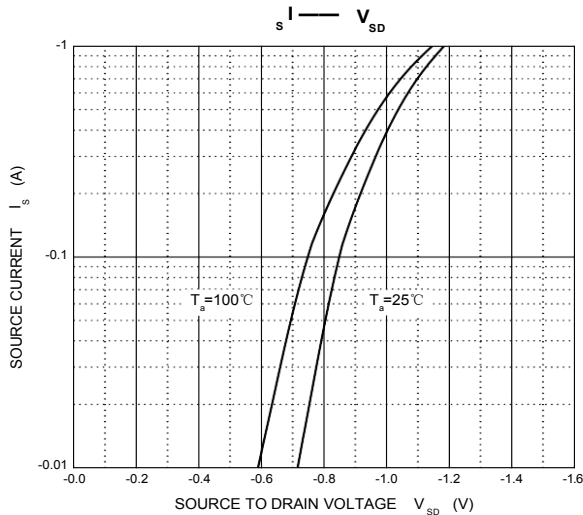
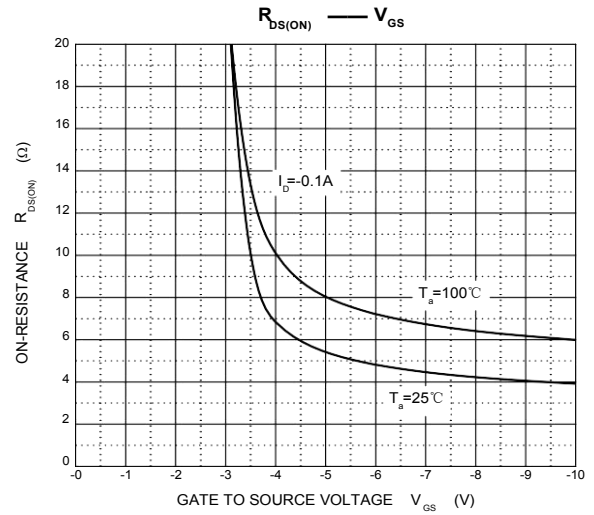
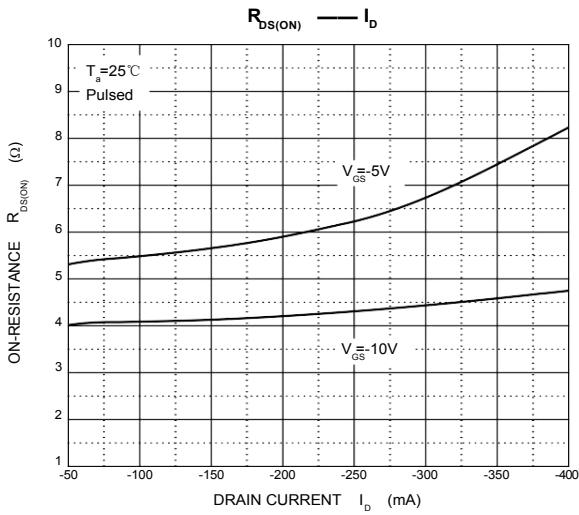
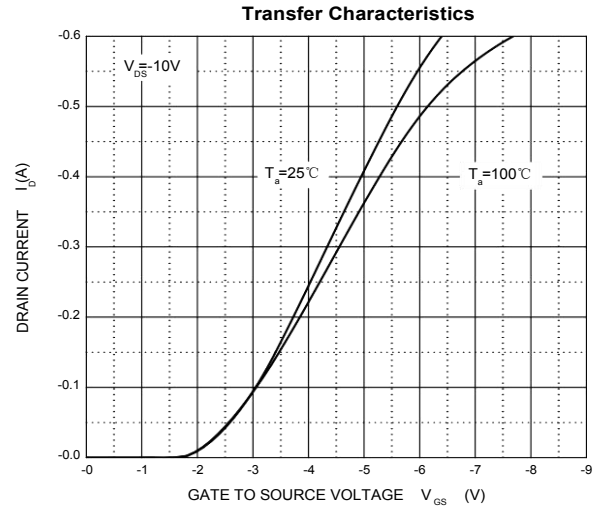
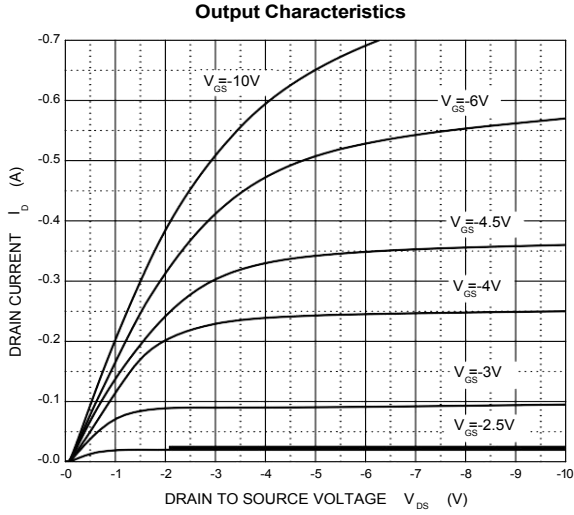
SOT-363

BSS84DW



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Typical Characteristics

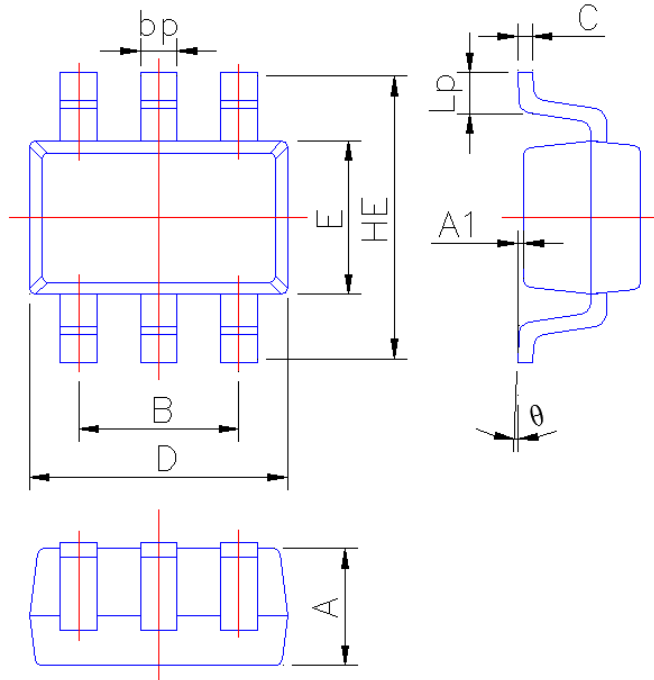




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-363



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
theta	0°	6°